

# Fang Song

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2139860/publications.pdf>

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#	ARTICLE	IF	CITATIONS
1	Physically Transient Resistive Memory With Programmable Switching Behaviors in MgO-Mo Based Devices. IEEE Electron Device Letters, 2020, 41, 553-556.	3.9	4
2	Physically Transient Memristor Synapse Based on Embedding Magnesium Nanolayer in Oxide for Security Neuromorphic Electronics. IEEE Electron Device Letters, 2019, 40, 1265-1268.	3.9	22
3	Physically Transient Resistive Switching Memory With Material Implication Operation. IEEE Electron Device Letters, 2019, 40, 1618-1621.	3.9	10
4	Physically Transient Memristive Synapse With Short-Term Plasticity Based on Magnesium Oxide. IEEE Electron Device Letters, 2019, 40, 706-709.	3.9	16
5	Solution-Processed Physically Transient Resistive Memory Based on Magnesium Oxide. IEEE Electron Device Letters, 2019, 40, 193-195.	3.9	23
6	ZnO-Based Physically Transient and Bioresorbable Memory on Silk Protein. IEEE Electron Device Letters, 2018, 39, 31-34.	3.9	42
7	A bio-inspired physically transient/biodegradable synapse for security neuromorphic computing based on memristors. Nanoscale, 2018, 10, 20089-20095.	5.6	82
8	Physically Transient Threshold Switching Device Based on Magnesium Oxide for Security Application. Small, 2018, 14, e1800945.	10.0	44
9	Polarization Engineering in PZT/AlGaIn/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2018, 65, 3149-3155.	3.0	16
10	Dissolvable and biodegradable resistive switching memory based on magnesium oxide. IEEE Electron Device Letters, 2016, , 1-1.	3.9	19